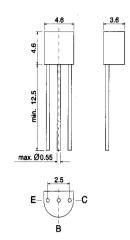
HN / 2N 3905/3906

PNP Silicon Expitaxial Planar Transistor for switching and amplifier applications.

As complementary types the NPN transistors HN / 2N3903 and HN / 2N 3904 are recommended.

On special request, these transistors can be manufactured in different pin configurations. Please refer to the "TO-92 TRANSISTOR PACKAGE OUTLINE" on page 80 for the available pin options.



TO-92 Plastic Package Weight approx. 0,18 g Dimensions in mm

Absolute Maximum Ratings (T_a= 25°C)

	Symbol	Value	Unit	
Collector Base Voltage	-V _{CBO}	40	V	
Collector Emitter Voltage	-V _{CEO}	40	V	
Emitter Base Voltage	-V _{EBO}	5	V	
Collector Current	-I _c	100	mA	
Peak Collector Current	-I _{CM}	200	mA	
Power Dissipation at T _{amb} = 25°C	P _{tot}	500¹)	mW	
Junction Temperature	T _J	150	∘C	
Storage Temperature Range	T _s	-55 to +150	°C	
1) Valid provided that leads are kept at ambient tem	perature at a distance of 2 mm f	rom case	,	

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Characteristics at T_{amb} =25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $-V_{CE} = 1V$, $-I_{C} = 0.1 \text{ mA}$	HN / 2N 3905 HN / 2N 3906	h _{FE}	30 60		- -	-
at $-V_{CE} = 1V$, $-I_{C} = 1$ mA	HN / 2N 3905 HN / 2N 3906	h _{FE}	40 80	-	-, -	- ·
at $-V_{CE} = 1V$, $-I_{C} = 10 \text{ mA}$	HN / 2N 3905 HN / 2N 3906	h _{FE}	50 100	-	150 300	-
at $-V_{CE} = 1V$, $-I_{C} = 50 \text{ mA}$	HN / 2N 3905 HN / 2N 3906	h _{FE}	30 60	-	-	-
at $-V_{CE} = 1V$, $-I_{C} = 100 \text{ mA}$	HN / 2N 3905 HN / 2N 3906	h _{FE}	15 30	- -	-	-
Thermal Resistance Junction to Amb	ient	R _{thA}	-	-	250 ¹)	K/W
Collector Saturation Voltage at $-I_c = 10$ mA, $-I_B = 1$ mA at $-I_c = 50$ mA, $-I_B = 5$ mA		-V _{CE} sat	- -	- -	0.25 0.4	V
Base Saturation Voltage at $-I_c = 10$ mA, $-I_B = 1$ mA at $-I_c = 50$ mA, $-I_B = 5$ mA		-V BE sat -V	-	-	0.85 0.95	V V
Collector Cutoff Current at -V _{EB} = 3 V, -V _{CE} = 30 V		-I _{CEV}	-	-	50	nA
Emitter Cutoff Current at -V _{EB} = 3 V, -V _{CE} = 30 V		-l _{EBV}	-	_	50	nA
Collector Base Breakdown Voltage at $-I_c = 10 \mu A$, $I_E = 0$		-V _{(BR)CBO}	40	-	-	٧
Collector Emitter Breakdown Voltage at $-I_c = 1$ mA, $I_B = 0$		-V _{(BR)CEO}	40	-	-	٧
Emitter Base Breakdown Voltage at -I _E = 10 μA, I _C = 0		-V _{(BR)EBO}	5	- ,	-	٧
Gain Bandwidth Product at -V _{CF} = 20 V, -I _C = 10 mA, f = 100Mh						
52 0	HN / 2N 3905 HN / 2N 3906	f _T	200 250	-	-	MHz MHz
Collector Base Capaçitance at -V _{CB} = 5V, f = 100 kHz		Ссво	-	-	4.5	pF
Emitter Base Capacitance at -V _{EB} = 0.5V, f = 100 kHz		C _{EBO}	-	-	10	pF

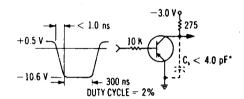


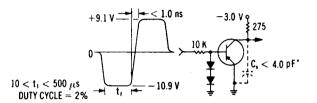




Characteristics (continued)

	Symbol	Min.	Тур.	Max.	Unit
Rise Time (see Fig. 1) at $-I_{B1} = 1$ mA, $-I_{C} = 10$ mA	t,	-	-	70	ns
Fall Time (see Fig. 2) at $I_{B1} = -I_{B2} = 1$ mA, $-I_{C} = 10$ mA	t, t,	-	-	200	ns ns





Flg. 1: Test circuit for delay and rise time * total shunt capacitance of test jig and connectors

Flg. 2: Test circuit for storage and fall time * total shunt capacitance of test jig and connectors

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